

256K x 16 HIGH SPEED ASYNCHRONOUS CMOS STATIC RAM WITH 3.3V SUPPLY

Description

The ISSI IS61LV25616AL is a high-speed, 4,194,304-bit static RAM organized as 262,144 words by 16 bits. It is fabricated using ISSI's high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields high-performance and low power consumption devices.

When \overline{CE} is HIGH (deselected), the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs, \overline{CE} and \overline{OE} . The active LOW Write Enable (\overline{WE}) controls both writing and reading of the memory. A data byte allows Upper Byte (\overline{UB}) and Lower Byte (\overline{LB}) access.

The device is offered in 10 and 12 ns access time options. Industrial temperature option is available.

The IS61LV25616AL is packaged in the JEDEC standard 44-pin 400-mil SOJ, 44-pin TSOP Type II, 44-pin LQFP and 48-pin Mini BGA (8mm x 10mm).

Additional Asynchronous SRAM Options

Den	Org	Part Number	Web link
1 Mb	64Kx16	IS61LV6416	http://www.issi.com/pdf/61LV6416_L.pdf
2 Mb	128Kx16	IS61LV12816L	http://www.issi.com/pdf/61LV12816L_LL.pdf
8 Mb	512Kx16	IS61LV51216	http://www.issi.com/pdf/61LV51216.pdf

About ISSI

ISSI is a fabless semiconductor company that designs and markets high performance integrated circuits for the following key markets: (i) digital consumer electronics, (ii) networking, (iii) mobile communications and (iv) automotive electronics. The company's primary products are high speed and low power SRAM and low and medium density DRAM. The company also designs and markets EEPROM, Pseudo SRAM and multi-chip packages and is developing selected non-memory products focused on its key markets. ISSI is headquartered in Silicon Valley with worldwide offices in Taiwan, China, Europe, Hong Kong, India and Korea.